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April 2014



FQA9N90C_F109

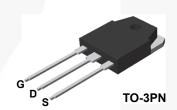
N-Channel QFET $^{\circledR}$ MOSFET 900 V, 9 A, 1.4 Ω

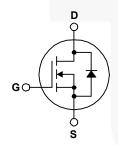
Features

- 9 A, 900 V, $R_{DS(on)}$ = 1.4 Ω (Max.) @ V_{GS} = 10 V, I_D = 4.5 A
- Low Gate Charge (Typ. 45 nC)
- Low Crss . 14 pF)
- 100% Avalanche Tested
- · RoHS compliant

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQA9N90C_F109	Unit	
V _{DSS}	Drain-Source Voltage		900	V	
I _D	Drain Current - Continuous (T _C = 25°C)		9.0	Α	
	- Continuous (T _C = 100°C)		5.7	Α	
I _{DM}	Drain Current - Pulsed	(Note 1)	36	Α	
V _{GSS}	Gate-Source Voltage		± 30	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	900	mJ	
I _{AR}	Avalanche Current	(Note 1)	9.0	Α	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	28	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3		4.0	V/ns	
P _D	Power Dissipation (T _C = 25°C)		280	W	
	- Derate above 25°C		2.22	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	FQA9N90C_F109	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.45	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA9N90C_F109	FQA9N90C	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Parameter Test Conditions		Тур.	Max.	Unit
Off Charac	teristics			I		
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	900			V
ΔBV _{DSS} / ΔΤ _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C		0.99		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 900 V, V _{GS} = 0 V			10	μА
		V _{DS} = 720 V, T _C = 125°C			100	μА
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Charact	teristics					•
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 4.5 A		1.12	1.4	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 50 V, I _D = 4.5 A		9.2		S
Dynamic Cl	haracteristics					
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,	\	2100	2730	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		175	230	pF
C _{rss}	Reverse Transfer Capacitance			14	18	pF
Switching C	Characteristics				I	
t _{d(on)}	Turn-On Delay Time	V _{DD} = 450 V, I _D = 11.0A,		50	110	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		120	250	ns
t _{d(off)}	Turn-Off Delay Time			100	210	ns
t _f	Turn-Off Fall Time	(Note 4)		75	160	ns
Qg	Total Gate Charge	V _{DS} = 720 V, I _D = 11.0A,		45	58	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V	/	13		nC
Q _{gd}	Gate-Drain Charge	(Note 4)	-	18		nC
Drain-Source	ce Diode Characteristics and Maximum Ratings		4		7	
I _S Maximum Continuous Drain-Source Diode Forward Current					9.0	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				36	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S =9.0 A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 9.0 A,		550		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		6.5		μС

Notes

 $^{{\}it 1. Repetitive\ rating: pulse-width\ limited\ by\ maximum\ junction\ temperature.}$

^{2.} L = 21 mH, I_{AS} = 9 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.

 $^{3.}I_{SD} \le 9$ A, di/dt ≤ 200 A/ μ s, $V_{DD} \le BV_{DSS}$, starting T_J = 25°C.

^{4.} Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

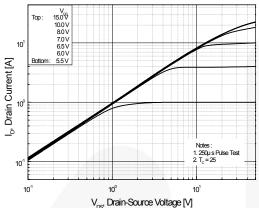


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

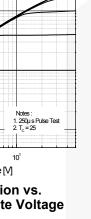


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

V_{ss}, Gate-Source Voltage [V]

Notes : 1. V_{DS} = 50V 2. 250µs Pulse Test

Figure 2. Transfer Characteristics

150°C

Drain Current [A]

10⁻¹ 2

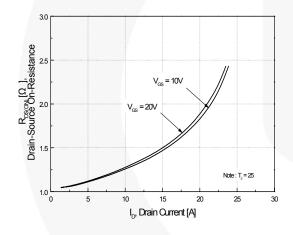
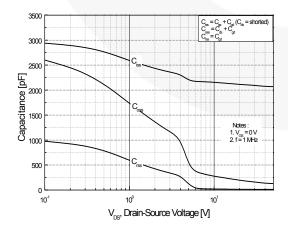
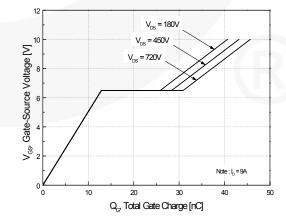


Figure 5. Capacitance Characteristics



Reverse Drain Current [A] Notes : 1. V_{cs} = 0V 2. 250µs Pulse Test 10⁻¹ 0.2 0.4 0.8 1.0 1.2 V_{SD}, Source-Drain voltage [V]

Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

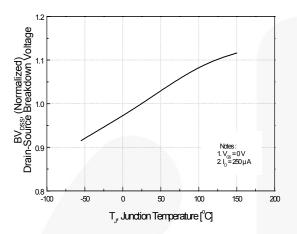


Figure 8. On-Resistance Variation vs. Temperature

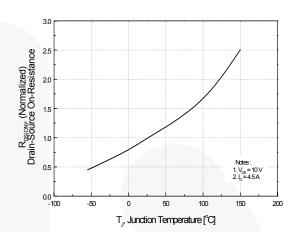
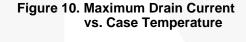
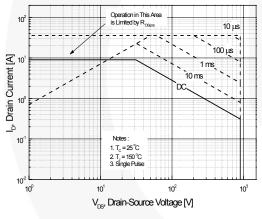


Figure 9. Maximum Safe Operating Area





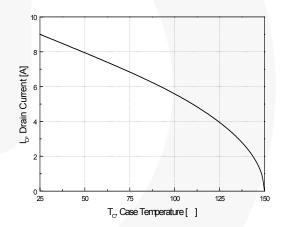
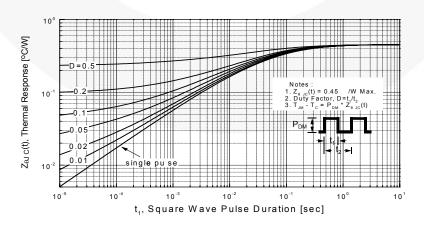


Figure 11. Transient Thermal Response Curve



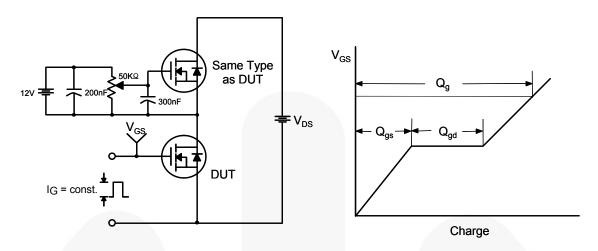


Figure 12. Gate Charge Test Circuit & Waveform

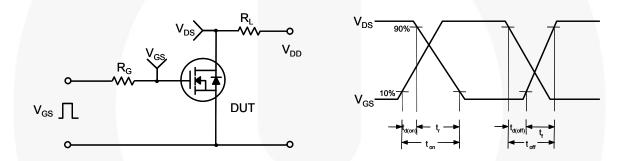


Figure 13. Resistive Switching Test Circuit & Waveforms

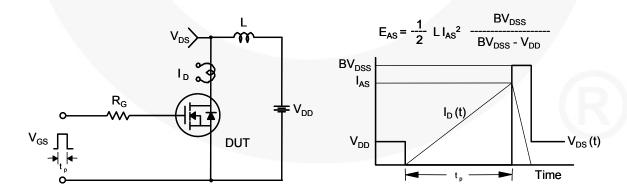


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

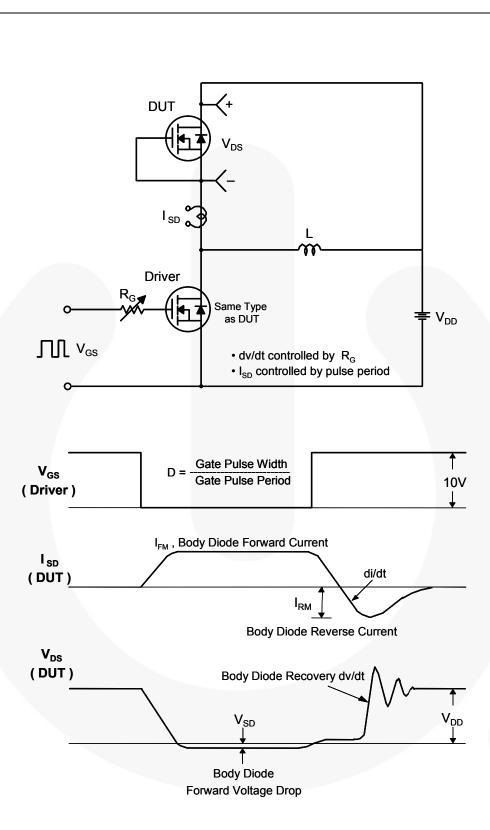


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

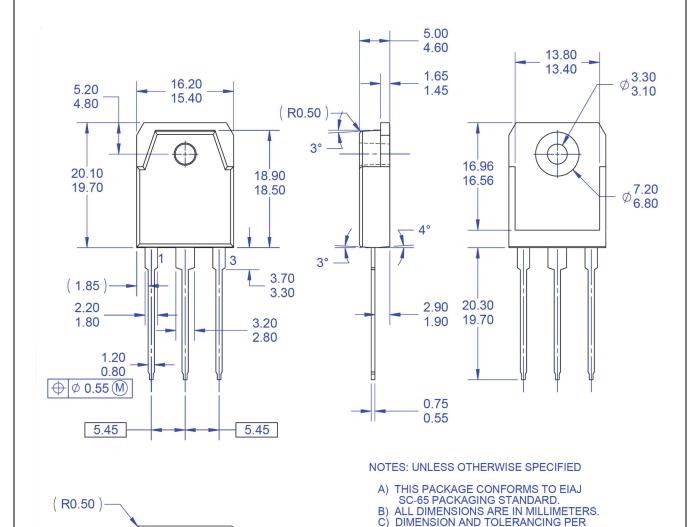


Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

ASME14.5-2009.

D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
E) DRAWING FILE NAME: TO3PN03AREV1.

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